Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1024	yamamoto-naoki.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 23:58
L2	10	yamamoto-naoki.inv. and nmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 00:00
L3	32	yamamoto-naoki.inv. and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 00:00
S1	2	"5683920".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:40
S2	2	"5780330".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:06
S3	2	"6300184".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:06
S4	2	"6503788".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:06
S5	2	"20020110969".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:10

S6	3	"6727132".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:11
S7	2	"6645799".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:11
S8	2	"6503788".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:12
S9	160	257/338.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:55
S10	1074	257/350.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:58
S11	642	257/351.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:00
S12	462	257/357.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:43
S13	1967	257/369.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:02

S14	649	257/371.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:05
S15	97	257/381.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:47
S16	1135	257/390.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:07
S19	242	(doped adj polysilicon) and (depth near concentration)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:54
S20	127	(doped adj polysilicon) and (depth near concentration) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 13:57
S21	0	(doped adj polysilicon) near segregated	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:11
S22	5	(doped adj polysilicon) with segregated	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:23
S23	187	(doped adj polysilicon) and cmos and ((wn or (tungsten nitride)) near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:26

S24	1	(doped adj polysilicon) and cmos and ((wn or (tungsten adj nitride)) near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:27
S25	88	(doped adj polysilicon) and cmos and ((wn or (tungsten adj nitride)) with gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:38
S26	2	(p adj n adj doped adj polysilicon) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:40
S27	0	(p adj n adj dopant adj polysilicon) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:41
S28	0	(p adj n adj diffused adj polysilicon) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:41
S29	1	(p adj n adj implanted adj polysilicon) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:42
S30	0	(p adj n adj impurity adj polysilicon) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:42
S31	0	(polysilicon adj doped adj boron adj phophorus) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:44

S32	0	((polysilicon adj doped) near boron near phophorus) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:44
S33	0	(polysilicon adj doped adj boron adj phosphorus) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:44
S34	0	((polysilicon adj doped) near boron near phosphorus) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:44
S35	8	((polysilicon adj doped) near boron near phosphorus)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:47
S36	2	((polysilicon adj doped) near boron near arsenic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:46
S37	0	((polysilicon adj doped) near boron near antimony)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:46
S38	54	((polysilicon adj doped) with boron with phosphorus)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:58
S39	1	((polysilicon adj implanted) with boron with phosphorus)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:58

S40	3	((polysilicon adj implanted) same boron same phosphorus)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:00
S41	127	((polysilicon adj doped) same boron same phosphorus)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:02
S42	0	((polysilicon adj doped) near (plurality adj dopants))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:02
S43	0	((polysilicon adj doped) with (plurality adj dopants))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:02
S44	0	((polysilicon adj doped) same (plurality adj dopants))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:03
S45	1110	257/412.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:09
S46	462	257/413.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:06
S47	12	tungsten near (tungsten adj nitride) near gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:21

S48	1094	tungsten with (tungsten adj nitride) with gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:21
S49	339	(tungsten with (tungsten adj nitride) with gate) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:37
S50	2	"5656519".pn. and (doped or dopant or impurity or implant$ or diffus$)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:38
S51	88	257/371.ccls. and (doped near polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:55
S52	24	257/338.ccls. and (doped near polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:55
S53	129	257/350.ccls. and (doped near polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 15:58
S54	88	257/351.ccls. and (doped near polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:02
S55	30	257/357.ccls. and (doped near polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:02

S56	206	257/369.ccls. and (doped near polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:03
S57	88	257/371.ccls. and (doped near polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:07
S58	22	257/381.ccls. and (doped near polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:07
S59	147	257/390.ccls. and (doped near polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:25
S60	191	257/412.ccls. and (doped near polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:19
S61	1	"6468872".pn. and polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:19
S62	0	"6468872".pn. and polycrystalline	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:19
S63	58	257/412.ccls. and (doped near polycrystalline near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:24

S64	24	257/413.ccls. and (doped near polycrystalline near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:24
S66	33	257/390.ccls. and (doped near polycrystalline near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:26
S67	8	257/381.ccls. and (doped near polycrystalline near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:27
S68	24	257/371.ccls. and (doped near polycrystalline near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:28
S69	73	257/369.ccls. and (doped near polycrystalline near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:29
S70	7	257/357.ccls. and (doped near polycrystalline near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:30
S71	31	257/351.ccls. and (doped near polycrystalline near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:30
S72	34	257/350.ccls. and (doped near polycrystalline near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:31

S73	3	257/338.ccls. and (doped near polycrystalline near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 16:31
S74	40	(doped adj polysilicon) same segregat$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:48
S75	11	(doped adj n adj p adj (impurity or dopant)) and polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:52
S76	175	(gated adj diode) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 17:54
S77	24	(segregat$ adj gate) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 18:05
S78	110	(segregat$ adj (dopants or impurities)) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 18:05
S79	3	(segregat$ adj (dopants or impurities)) near gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 18:06
S80	801	(segregat$ adj (dopants or impurities))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 18:06

S81	110	(segregat$ adj (dopants or impurities)) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 19:43
S83	17	anneal$ same hydrogen same vapor same segregat$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 20:13
S84	0	"6468872".pn. and melt$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 20:14
S85	0	"6468872".pn. and anneal$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 20:14
S86	0	"6468872".pn. and hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 20:42
S87	1	"5656519".pn. and (boron or phosphorus or arsenic or antimony)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 21:01
S88	45	((silicon adj oxynitride) near (gate adj (oxide or insulat$ or dielectric))) and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 23:53